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In the Claims:

1 1. (Previously presented) A semiconductor light emitting
2 device of a II-VI group compound semiconductor formed on a
3 compound semiconductor substrate and comprising an active
4 layer between an n-type cladding layer and a p-type
5 cladding layer, further comprising

6 an i-type semiconductor barrier layer consisting of a
7 single monolayer of an i-type semiconductor material having
8 a band gap larger than a band gap of said p-type cladding
9 layer, provided between and respectively directly in
10 contact with said active layer and said p-type cladding
11 layer.

1 2. (Withdrawn) The semiconductor light emitting device
2 according to claim 1, wherein

3 said light emitting device of the II-VI group compound
4 is a ZnSe based light emitting device;

5 said n-type cladding layer is an n-type $\text{Zn}_{1-x}\text{Mg}_x\text{S}_y\text{Se}_{1-y}$
6 ($0 < x < 1$, $0 < y < 1$) layer; and

7 said p-type cladding layer is a p-type $\text{Zn}_{1-x}\text{Mg}_x\text{S}_y\text{Se}_{1-y}$
8 ($0 < x < 1$, $0 < y < 1$) layer.

1 3. (Original) The semiconductor light emitting device
2 according to claim 1, wherein

3 magnitude of the band gap of said barrier layer is
4 larger by 0.025 eV to 0.5 eV than the band gap of said
5 p-type cladding layer.

1 4. (Previously presented) The semiconductor light emitting
2 device according to claim 1, wherein

3 in the band gap of said barrier layer, energy of
4 valence band is approximately the same as or higher than
5 that of said p-type cladding layer, and energy of
6 conductive band is larger than that of said p-type cladding
7 layer.

1 5. (Original) The semiconductor light emitting device
2 according to claim 1, wherein

3 said barrier layer is of a II-VI group compound
4 semiconductor containing Be.

1 6. (Original) The semiconductor light emitting device
2 according to claim 5, wherein

3 said barrier layer is of $\text{Zn}_{1-x-y}\text{Mg}_x\text{Be}_y\text{Se}$ ($0 \leq x + y \leq 1$,
4 $0 < x$, $0 < y$).

1 7. (Withdrawn) The semiconductor light emitting device
2 according to claim 1, wherein

3 said barrier layer is of $\text{Zn}_{1-x}\text{Mg}_x\text{S}_y\text{Se}_{1-y}$.

Claims 8 to 10 (Canceled).

1 11. (Original) The semiconductor light emitting device
2 according to claim 1, wherein

3 said p-type cladding layer is formed of
4 $(\text{Zn}_{1-x}\text{Cd}_x\text{S})_{1-z}(\text{MgS}_{1-y}\text{Se}_y)_z$ (where x, y, z satisfy $0 < x \leq 1$,
5 $0 \leq y \leq 1$, $0 \leq z < 1$).

1 12. (Original) The semiconductor light emitting device
2 according to claim 1, wherein

3 thickness of said barrier layer is at least 5 nm and
4 at most thickness of said active layer.

1 13. (Original) The semiconductor light emitting device
2 according to claim 1, wherein

3 an n-type ZnSe single crystal substrate is used as
4 said compound semiconductor substrate.

1 14. (Withdrawn) The semiconductor light emitting device
2 according to claim 1, wherein

3 an n-type GaAs single crystal substrate is used as
4 said compound semiconductor substrate.

1 15. (Withdrawn) The semiconductor light emitting device
2 according to claim 1, wherein

3 in a stacked structure including said compound
4 semiconductor substrate constituting said ZnSe based light
5 emitting device, deviation between a peak of X-ray
6 diffraction of a plane orientation used as an index of
7 distortion from said substrate and a peak of X-ray

8 diffraction of said plane orientation from said stacked
9 structure is at most 1000 seconds.

Claims 16 to 25 (Canceled).

1 26. (New) The semiconductor light emitting device according to
2 claim 1, wherein said cladding layers, said active layer,
3 and said i-type semiconductor material of said barrier
4 layer each respectively comprise a respective group II-VI
5 compound semiconductor material.

1 27. (New) The semiconductor light emitting device according to
2 claim 1, wherein said barrier layer consists of said i-type
3 semiconductor material which is $\text{Zn}_{1-x-y}\text{Mg}_x\text{Be}_y\text{Se}$ ($0 < x$, $0 < y$,
4 $x+y \leq 1$), and said barrier layer has a layer thickness of
5 at least 5nm.

[RESPONSE CONTINUES ON NEXT PAGE]